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Simulation of the growth of CVD films

Jacob J. Thiart
Department of Chemical Engineering, Suny at Buffalo, Amhearst, 14260

Vladimir Hlavacek
Department of Chemical Engineering, State university of New York, Buffalo. NY

Hendrik J. Viljoen
Department of Chemical Engineering, University of Nebraska-Lincoln, hviljoen1@unlnotes.unl.edu

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1. INTRODUCTION

Chemical vapor deposition (CVD) is the preferred method of manufacture for solid films used in many industrially important thin and thick film applications. Requirements for the physical, mechanical and electrical properties of these films are becoming increasingly difficult to achieve, and deposition morphology plays an important role in this regard. Recently, we proposed a continuum model describing the evolution of a gas-solid interface during atmospheric pressure CVD (Viljoen et al., 1994). A linear stability analysis (LSA) was used to determine the effect of reactor conditions on planar growth stability. The present paper discusses numerical solution of this model, and uses simulation examples to illustrate interface evolution under typical deposition conditions and from arbitrary initial interface shapes.

2. MODEL FORMULATION

We consider the growth of an amorphous solid film during a typical high pressure (0.1-1 atm), low Knudsen number ($K_n \ll 1$) CVD process. Transport of gaseous species to the interface is assumed to be diffusive. Details of the model derivation are given in Viljoen et al. (1994) and only the final dimensionless governing equations are presented here. The gas phase concentration balance becomes:

$$\frac{\partial C}{\partial t} = \frac{1}{Pe} \left( \frac{\partial^2 C}{\partial z^2} + \frac{\partial C}{\partial z} \right)$$

and the interface evolution equation (solid phase):

$$\frac{\partial H}{\partial t} = \frac{\rho}{Pe} (\nabla \cdot n) \sqrt{1 + H^2} - 1 + \kappa \left[ \frac{H}{\sqrt{1 + H^2}} \right]$$

with boundary conditions

$$\frac{\partial C}{\partial z} = \frac{\partial C}{\partial z} = 0$$

$$\varphi(0, \zeta) - \varphi(n', \zeta) \quad \text{where} \quad n = 0, \pm 1, \pm 2, \ldots$$

$$\frac{1}{Pe} (\nabla \cdot n) = \gamma \left[ 1 - \frac{\Gamma}{\kappa} \right] \varphi \quad \text{at} \quad \zeta = H$$

and where

$$\kappa = -\frac{H_{ss}^2}{(1 + H_{ss}^2)^{3/2}} \cdot \frac{V_0 L}{D_f}, \quad \gamma = \frac{kN_{ss} s}{D_f}.$$
explicit solution method. Stability requirements dictate a small time step, and the maximum time step can be determined with a formula similar to that defined for parabolic equations (see e.g. Finlayson [1980]). In our case, however, spatial derivatives up to fourth order are present in the surface diffusion term. This is not common in chemical engineering applications, where typically reaction-diffusion or convection-diffusion problems are encountered. Higher derivatives tend to amplify the effect of kinks in the interface. Computational problems can usually be avoided by flooding problem areas with many points. Unfortunately, this decreases the maximum allowable time step. For example, if the number of points are doubled, the time step has to be reduced about sixteen times. For time integration a fourth order Runge-Kutta method with automatic time step adjustment was used.

4. NUMERICAL EXAMPLES

With periodic boundary conditions, one can in principle choose any length of substrate on which to study deposition. However, if this length is too small, the results may not be representative of a real case. The horizontal length is therefore chosen 5 to 20 times larger than the wavelength associated with the "most" unstable perturbation. The latter is the perturbation associated with the largest eigenvalue in the LSA under the specific conditions [see Viljoen et al. (1994)]. Consider a CVD process with parameters in the range typical for the CVD growth of e.g. SiC and CrB, thus atmospheric pressure and temperatures higher than 900 K. Typical parameter values are given in Table 1. For these parameters and at a temperature of 1100 K the wavelength of most unstable perturbation (as determined from LSA) is 85.2 pm. Therefore, an acceptable horizontal length to choose as solution domain is 500 pm.

Another important characteristic is the following. We can use the LSA to determine the time needed to double the amplitude of a protrusion with most unstable wavelength, which is the dominant one at short deposition times. At 1100 K this time is 142 h, which means that in the typical duration of deposition we will not observe a significant change in planar morphology even though planar deposition is unstable under those conditions. This situation changes drastically for deposition at 1600 K, where the wavelength of most unstable perturbation is 7.6 pm. The time to double the amplitude is now only 140 s, which means very significant changes in the morphology will take place in normal operating times.

Now consider a case where the substrate has a random initial roughness onto which a film is deposited. The effect of temperature and Damkohler number on the morphology of film growth is shown in Fig. 1. Note that the duration of each run is different, since the deposition rate increases with increasing Damkohler number. The morphology of the films grown at $Da = 1/20$ and $Da = 1$ is very similar, but both cases are quite different than the run for $Da = 20$. At low to moderate Damkohler numbers the initial randomly rough surface develops into a characteristic nodular structure, which is commonly observed in CVD experiments (Vandenbulcke and Vuillard, 1976; Chin et al., 1977; Schmidt, 1991). The results indicate that larger nodules grow at the expense of smaller ones. This growth-death phenomenon is commonly observed in deposition processes (Messier, 1986). It

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Value</th>
</tr>
</thead>
<tbody>
<tr>
<td>$\gamma$ (m)</td>
<td>$10^{-3}$</td>
</tr>
<tr>
<td>$\delta$ (m)</td>
<td>$10^{-8}$</td>
</tr>
<tr>
<td>$kK_d$ (m/s)</td>
<td>$2 \times 10^5 \exp[-(24056/T)^{1/2}]$</td>
</tr>
<tr>
<td>$D_f$ (m$^2$/s)</td>
<td>$10^{-16}T^{1.823}$</td>
</tr>
<tr>
<td>$D_r$ (m$^2$/s)</td>
<td>$\exp[-2000/T(5.0 + 0.00337T)]$</td>
</tr>
<tr>
<td>$\Gamma$ (m)</td>
<td>$8 \times 10^{-7}/T$</td>
</tr>
</tbody>
</table>

Table 1. System parameters for typical CVD process

Fig. 1. Effect of temperature and thus Damkohler number on uniformity of film growth at a constant pressure of 1 atm: (a) $Da = 1/20$, (b) $Da = 1$, (c) $Da = 20$. Although moderate Damkohler numbers the initial roughness onto which a film is deposited. The effect of temperature and Damkohler number on the morphology of film growth is shown in Fig. 1. Note that the duration of each run is different, since the deposition rate increases with increasing Damkohler number. The morphology of the films grown at $Da = 1/20$ and $Da = 1$ is very similar, but both cases are quite different than the run for $Da = 20$. At low to moderate Damkohler numbers the initial randomly rough surface develops into a characteristic nodular structure, which is commonly observed in CVD experiments (Vandenbulcke and Vuillard, 1976; Chin et al., 1977; Schmidt, 1991). The results indicate that larger nodules grow at the expense of smaller ones. This growth-death phenomenon is commonly observed in deposition processes (Messier, 1986). It
has been shown that the dominant nodule size follows a power law relation with respect to the film thickness, thus $D_n = \alpha t^\varepsilon$, where $D_n$ is the dominant nodule size, $t$ the time of deposition or film thickness, and $\varepsilon$ an exponent which depends on deposition conditions. For the run at $Da = 1$ the exponent is found to be $\varepsilon = 0.64$, which compares well with

Fig. 3. Effect of temperature and thus Damkohler number on step coverage in a trench at a constant pressure of 1 atm:
(a) $Da = 1/20$, (b) $Da = 1$, (c) $Da = 20$.  

Fig. 2. Iso-concentration lines for deposition conditions in Fig. 1.
the predicted value of Kardar et al. (1986). They solved a simplified growth model analytically and found the exponent to be $\epsilon = 2/3$.

At $\text{Da} = 20$ interface growth does not seem to follow the typical growth-death phenomenon. Nodules tend to develop into long fingers with deep grooves between them. This has been observed experimentally in the CVD growth of Si from SiHCl$_3$ in the gas phase (van den Brekel, 1977) under diffusion-limited conditions. It is also similar to dendritic growth observed in solidification experiments where evolution of the liquid-solid interface is driven by diffusion of heat (Huang and Glicksman, 1981a, b). The formation of grooves is caused by depletion of reactant under diffusion-limited conditions. Note the tendency of some fingers to nose ahead of their neighbors. This is clear from Fig. 1(c), where reactant at the tip of the second nodule (at about the $-140\mu$m position) is depleted and growth therefore inhibited. Iso-concentration lines for the runs mentioned above are shown in Fig. 2. Note how the reactant concentration close to the interface changes with increasing Damköhler number. At $\text{Da} = 1/20$, it is close to the value in the bulk and at $\text{Da} = 20$ it is close to zero.

When finger formation takes place, gradients of the interface ($\partial H / \partial c$) along the sides of fingers become very large and can in fact approach infinity. The growth model represents height of the interface $H$ as a single-valued function of horizontal coordinate $x$, and it is therefore assumed $\partial H / \partial x$ is finite. As a result, computational problems are encountered when gradients become very large. To solve this problem, one can reformulate the model in a parametric form, where a different parameter than the horizontal coordinate is used. This will be addressed elsewhere.

Now consider a case where the initial interface is in the form of a deep trench. This shape is typically found in the electronics industry, but the length scale may be quite different. It is often required that the thickness on all sides of the trench be the same. This requirement can be expressed in terms of the step coverage (Oh et al., 1992), which represents the ratio of film thickness in the bottom of the trench to that at the top of the trench. The effect of temperature and thus the Damköhler number on the film growth in a trench is shown in Fig. 3. Deposition parameters and physical properties were the same as in Table 1 and $1000\mu$m of the substrate was considered. The results clearly illustrate that step coverage decreases with increasing Damköhler number, which is similar to decrease in film uniformity observed in the previous example.

The runs in Fig. 3 were conducted at a constant pressure of 1 atm. Suppose one wants to maintain the high deposition temperature but improve step coverage at that temperature by adjusting other parameters, such as reactant dilution ratio or pressure. At such a high temperature the deposition is diffusion-limited, so step coverage should improve if the diffusional limitation can be decreased. Gas diffusion is inversely related to reactor pressure, which means step coverage should improve if the reactor pressure is decreased at constant dilution ratio. Three runs at different pressure and constant temperature of 1443 K were performed and the results are shown in Fig. 4. The graphs indicate that the step coverage indeed improves. Note that the Damköhler number decreases linearly with decreasing pressure.

**Fig. 4.** Effect of reactor pressure on step coverage of a trench under diffusion-limited conditions: (a) $P = 1.0\text{ atm}$, (b) $P = 0.5\text{ atm}$, (c) $P = 0.1\text{ atm}$.

**5. CONCLUSIONS**

Numerical solution of a continuum model derived for the evolution of a gas-solid interface during atmospheric pressure CVD is described. Simulation results showed that deposition morphology is strongly dependent on the Damköhler number, $\text{Da}$. A significant decrease in film uniformity was observed for increasing values of the $\text{Da}$ This trend was also observed for growth in a trench, where step coverage was found to decrease with increasing values of $\text{Da}$. Under diffusion-limited conditions, step coverage was found to improve if the diffusional limitations could be decreased by decreasing system pressure at constant substrate temperature. The numerical results suggest that film uniformity and optimal step coverage can be achieved by changing operating condi-
tions in such a way that the lowest value of a Damköhler number of deposition is achieved.

JACOB J. THIART,
VLADIMIR HLAVACEK

Laboratory of Ceramic and Reaction Engineering
Department of Chemical Engineering
C.C. Furnas Hall
State University of New York at Buffalo
Amherst, NY 14260, U.S.A.

HENDRIK J. VILJOEN
Department of Chemical Engineering
University of Nebraska at Lincoln
Lincoln, NE 68588-0126, U.S.A.

NOTATION

$C$ dimensionless concentration, subscript b-built
$D$ diffusion coefficient, subscripts: f—gas, m$^2$/s; e—surface, m$^2$/s
$Da$ Damköhler number, defined as $kK_{ad}/D_f$ or $Pe/L$
$H$ dimensionless height of film
$kK_{ad}$ rate constant, m/s
$l$ dimensionless length of film, considered, period
$L$ characteristic length scale, $\sqrt{D_f/2V_0}$, m
$Pe$ Peclet number, $V_fL/D_f$
$s$ boundary layer thickness, m
$V_0$ reference deposition rate, m/s

Greek letters

$V$ molar volume, m$^3$/mole
$\Gamma$ capillary length, m
$\delta$ radius of molecule, m
$\zeta$ vertical coordinate, dimensionless
$\vartheta$ dimensionless parameter, defined as $kK_{ad}/V_0$
$k$ dimensionless surface curvature,
$H_{ss} = \frac{1}{(1 + H_{f} + H_{a})^{3/2}}$
$\xi$ horizontal coordinate, dimensionless
$\rho$ dimensionless parameter, equivalent to $\gamma C_a$
$\tau$ dimensionless time, $V_f/s/L$
$\chi$ dimensionless parameter, equivalent to $D_f/V_f L^2$

REFERENCES